



《风光欣》技术资料

C945

NPN EPITAXIAL SILICON TRANSISTOR

AUDIO FREQUENCY AMPLIFIER

HIGH FREQUENCY OSC

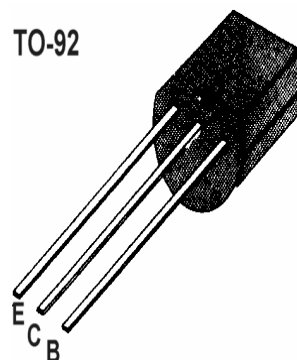
*Complement to A733

*Collector-Base Voltage VCBO=60V

*High Current Gain Bandwidth Prodeut $f_T=300\text{MHZ}(\text{Typ})$

ABSOLUTE MAXIMUM RATINGS(TA=25)

T0-92



Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	VCBO	60	V
Collector-Emitter Voltage	VCEO	50	V
Emitter -Base Voltage	VEBO	5	V
Collector Current	Ic	150	mA
Collector Dissipation	Pc	250	mW
Junction Temperature	TJ	150	
Storage Temperature	TSTG	-55 ~150	

ELECTRCAL CHARACTERISTICS(TA=25)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage	BVCBO	Ic=100 μ A, IE=0	60			V
Collector-Emitter Breakdown Voltage	BVCEO	Ic=10mA, IB=0	50			V
Emitter-Base Breakdown Voltage	BVEBO	IE=10 μ A, Ic=0	5			V
Collector Cut-off Current	ICBO	VCB= 40V, IE=0			0.1	μ A
Emitter Cut-off Current	IEBO	VEB= 3V, Ic=0			0.1	μ A
DC Current Gain	HFE	VCE= 6V, Ic= 1.0mA	40		700	
Collector-Emitter Saturation Voltage	VCE(sat)	Ic= 100mA, IB= 10mA		0.15	0.3	V
Current Gain-Bandwidth Product	fT	VCE= 6V, Ic= 10mA		300		MHz
Output Capacitance	COB	VCB= 6V, IE= 0, F=1MHZ		2.5		pF

Hfe CLASSIFICATION

Classification	R	O	Y	G	L
HFE	40-80	70-140	120-240	200-400	350-700